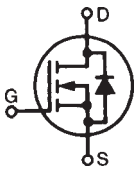
IXYS

PolarHT™ HiPerFET Power MOSFET

IXFH 100N25P

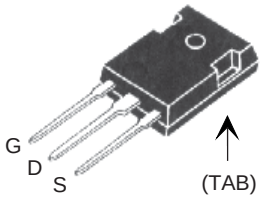
V_{DSS} = 250 V
I_{D25} = 100 A
$R_{DS(on)}$ ≤ 27 mΩ
t_{rr} ≤ 200 ns

N-Channel Enhancement Mode
Fast Intrinsic Diode
Avalanche Rated



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	250	V
V_{DGR}	T_J = 25°C to 150°C; R_{GS} = 1 MΩ	250	V
V_{GS}	Continuous	±20	V
V_{GSM}	Transient	±30	V
I_{D25}	T_C = 25°C	100	A
$I_{D(RMS)}$	External lead current limit	75	A
I_{DM}	T_C = 25°C, pulse width limited by T_{JM}	250	A
I_{AR}	T_C = 25°C	60	A
E_{AR}	T_C = 25°C	60	mJ
E_{AS}	T_C = 25°C	2.0	J
dv/dt	$I_S \le I_{DM}$, di/dt ≤ 100 A/μs, $V_{DD} \le V_{DSS}$, $T_J \le 150°C$, R_G = 4 Ω	10	V/ns
P_D	T_C = 25°C	600	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	1.6 mm (0.062 in.) from case for 10 s	300	°C
T_{SOLD}	Plastic body for 10 s	260	°C
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight		5.5	g

TO-247 (IXFH)



G = Gate D = Drain
S = Source TAB = Drain

Features

- Fast Intrinsic Diode
- International standard packages
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
  - easy to drive and to protect

Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0 V, I_D = 250 μA	250			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 4 mA	2.5		5.0	V
I_{GSS}	V_{GS} = ±20 V_{DC}, V_{DS} = 0			±100	nA
I_{DSS}	$V_{DS} = V_{DSS}$, V_{GS} = 0 V			25	μA
	T_J = 125°C			500	μA
$R_{DS(on)}$	V_{GS} = 10 V, $I_D = 0.5\ I_{D25}$, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			27	mΩ

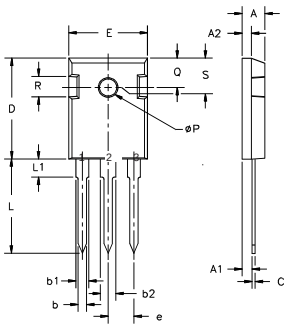
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Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) Min.	Typ.	Max.	
g_{fs}	V_{DS}= 10 V; I_D = 0.5 I_{D25}, pulse test	40	56		S
C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		6300		pF
C_{oss}			1150		pF
C_{rss}			240		pF
$t_{d(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D = I_{D25} R_G = 3.3 Ω (External)		25		ns
t_r			26		ns
$t_{d(off)}$			100		ns
t_f			28		ns
$Q_{g(on)}$	V_{GS}= 10 V, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}		185		nC
Q_{gs}			43		nC
Q_{gd}			91		nC
R_{thJC}				0.21	°C/W
R_{thCS}			0.25		°C/W

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) Min.	Typ.	Max.	
I_S	V_{GS} = 0 V			100	A
I_{SM}	Repetitive			250	A
V_{SD}	I_F = I_S, V_{GS} = 0 V, Pulse test, t ≤ 300 µs, duty cycle d ≤ 2 %			1.5	V
t_{rr}	I_F = 25 A, -di/dt = 100 A/µs V_R = 100 V			200	ns
Q_{RM}			0.6		µC
I_{RM}			10		A

TO-247 (IXFH) Outline



Terminals: 1 - Gate 2 - Drain
3 - Source Tab - Drain

Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.7	5.3	.185	.209
A_1	2.2	2.54	.087	.102
A_2	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b_1	1.65	2.13	.065	.084
b_2	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15 BSC		242 BSC	

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or moreof the following U.S. patents: 4,835,592 4,850,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123 B1 6,306,728 B1 6,404,065 B1 6,534,343 6,583,505 6,683,344 6,710,405B2 6,710,463 6,727,585 6,759,692 6,771,478 B2

Fig. 1. Output Characteristics @ 25ºC

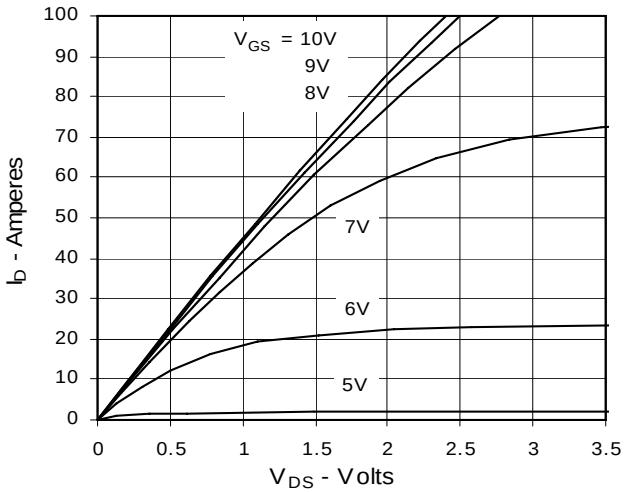


Fig. 2. Extended Output Characteristics @ 25ºC

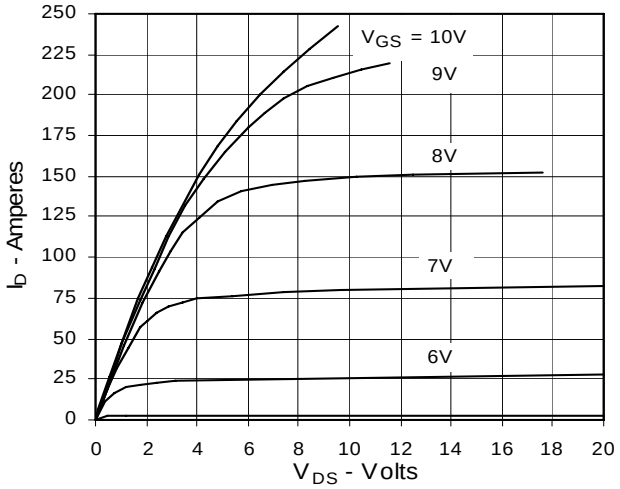


Fig. 3. Output Characteristics @ 125ºC

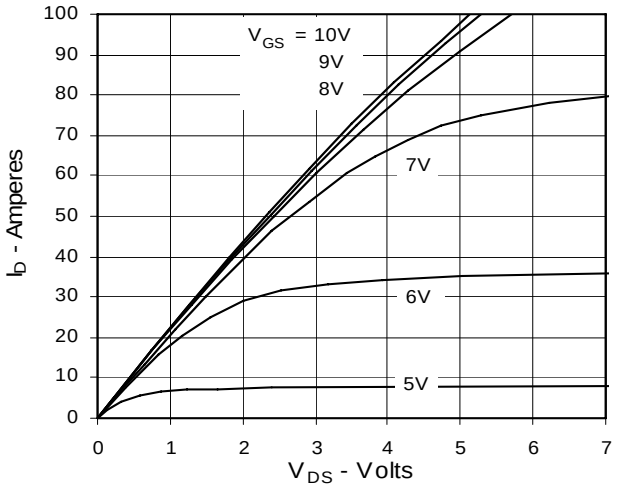


Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. Junction Temperature

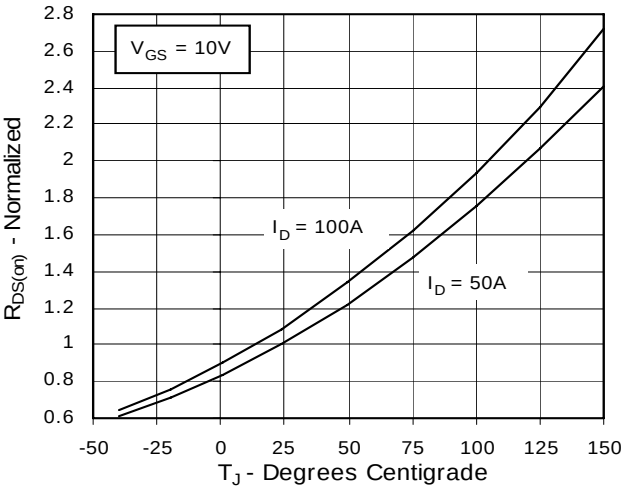


Fig. 5. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. I_D

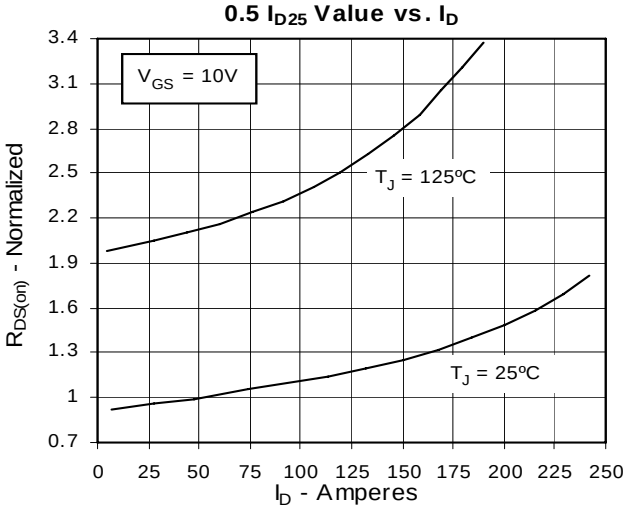
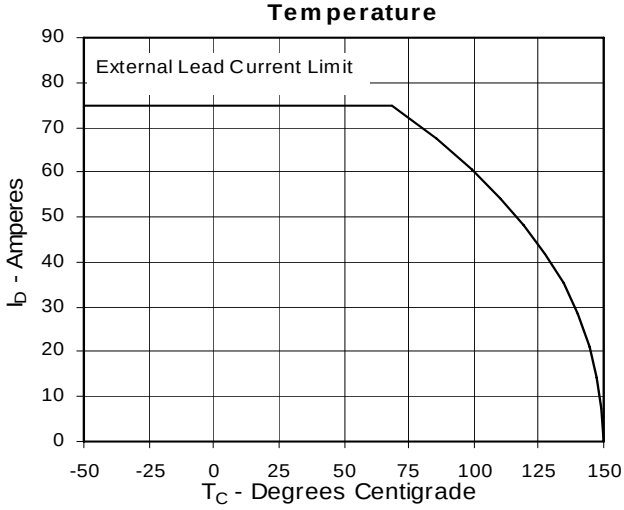


Fig. 6. Drain Current vs. Case Temperature



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Fig. 7. Input Admittance

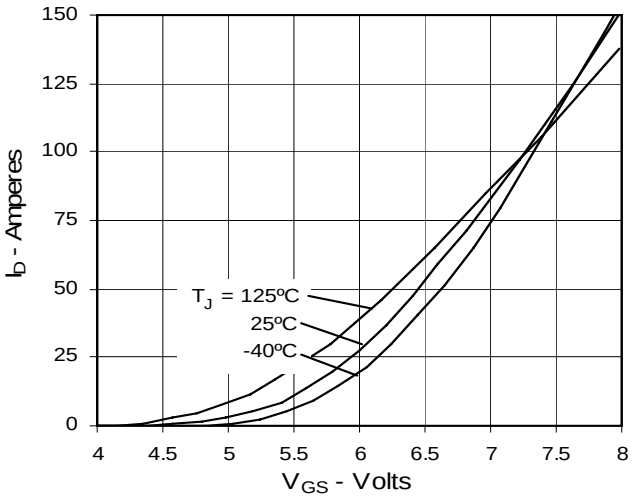


Fig. 8. Transconductance

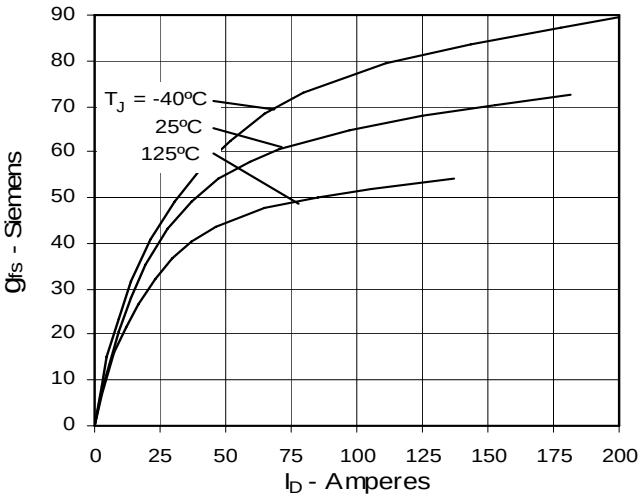


Fig. 9. Source Current vs. Source-To-Drain Voltage

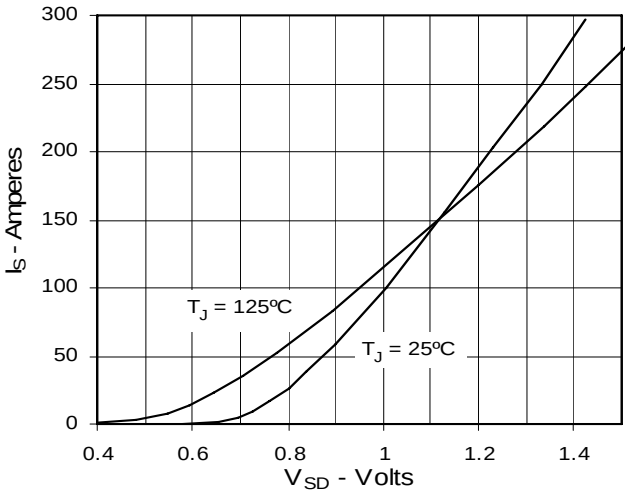


Fig. 10. Gate Charge

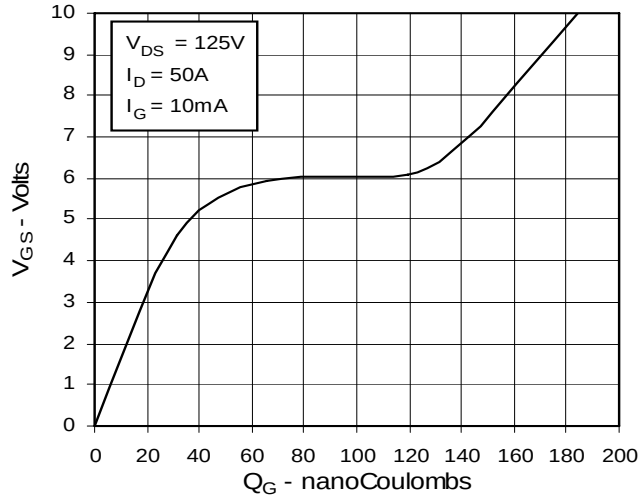


Fig. 11. Capacitance

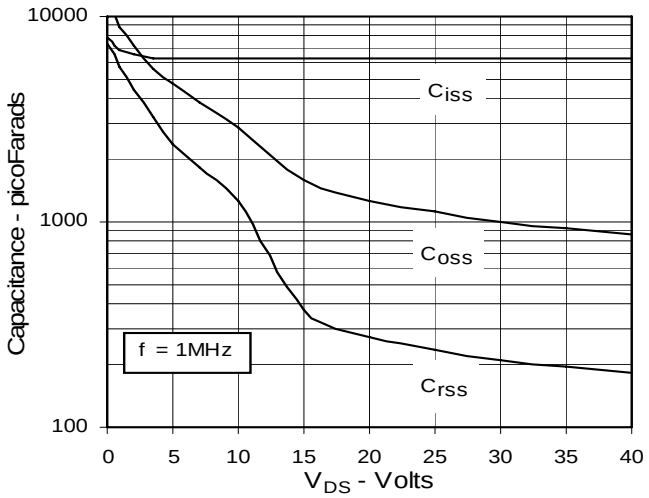
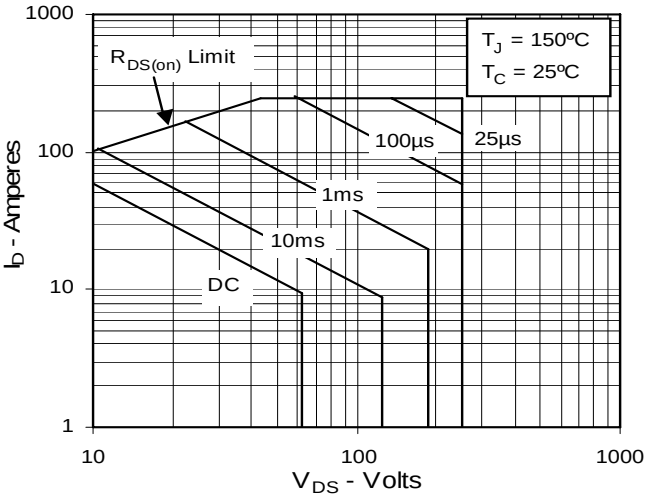
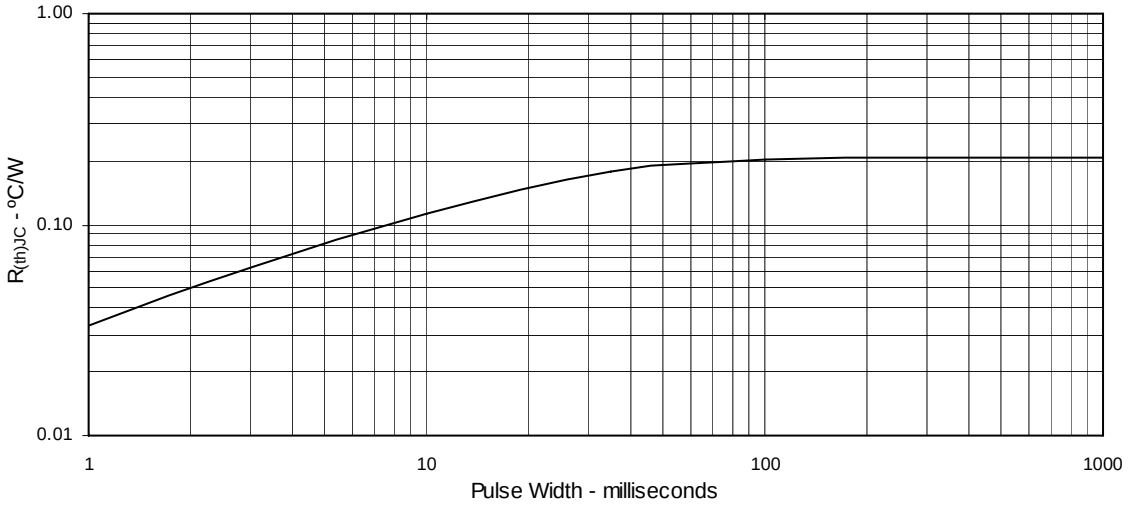


Fig. 12. Forward-Bias Safe Operating Area



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Fig. 13. Maximum Transient Thermal Resistance



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